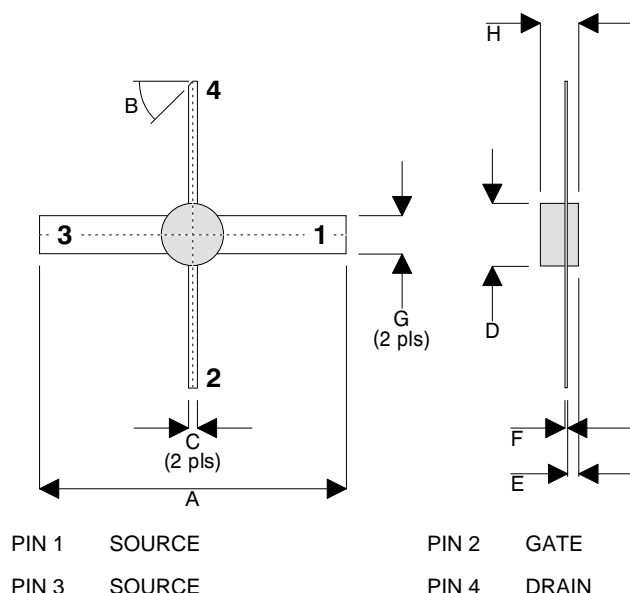


MECHANICAL DATA



DIM	Millimetres	Tol.	Inches	Tol.
A	25.40	0.25	1.00	0.010
B	45°	5°	45°	5°
C	0.76	0.05	0.030	0.002
D	5.21 DIA	0.13	0.205	0.005
E	1.02	0.13	0.040	0.005
F	0.13	0.02	0.005	0.001
G	3.18	0.13	0.125	0.005
H	3.18	REF	0.125	REF

GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 1W – 28V – 2GHz SINGLE ENDED

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
from DC to 2 GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	4W
BV_{DSS}	Drain – Source Breakdown Voltage	65V
BV_{GSS}	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	1A
T_{stg}	Storage Temperature	-65 to $150^{\circ}C$
T_j	Maximum Operating Junction Temperature	$200^{\circ}C$

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS} Drain–Source Breakdown Voltage	V _{GS} = 0 I _D = 10mA	65			V
I _{DSS} Zero Gate Voltage Drain Current	V _{DS} = 28V V _{GS} = 0			1	mA
I _{GSS} Gate Leakage Current	V _{GS} = 20V V _{DS} = 0			1	μA
V _{GS(th)} Gate Threshold Voltage	I _D = 10mA V _{DS} = V _{GS}	1		7	V
g _{fs} Forward Transconductance*	V _{DS} = 10V I _D = 0.2A	0.18			mhos
P _{out} Power Output	V _{DS} = 28V I _{DQ} = 75mA f = 30MHz P _{in} = 5mW	750			mW
C _{iss} Input Capacitance	V _{DS} = 0V V _{GS} = –5V f = 1MHz			12	pF
C _{oss} Output Capacitance	V _{DS} = 28V V _{GS} = 0 f = 1MHz			6	
C _{rss} Reverse Transfer Capacitance				0.5	

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 30°C / W
-----------------------	------------------------------------	---------------